

-30V P-Channel MOSFET

General Features

- Advanced groove technology is adopted
- Provide excellent RDS(ON)
- Low gate charge and operate at low gate voltage

Application

- Lithium battery protection
- Wireless impact
- Mobile phone fast charging

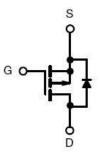


Product Summary

BVDSS	-30	V
RDS(on).Typ.@VGS=-10V	5.0	mΩ
ID	-100	Α



TO-252-2L top view



Schematic diagram

Absolute Maximum Ratings (TC=25℃unless otherwise noted)

Symbol	Parameter	Max.	Units
VDSS	Drain-Source Voltage	-30	V
VGSS	Gate-Source Voltage	±20	V
ID	Continuous Drain Current $T_C = 25^{\circ}C$	-100	А
ID	Continuous Drain Current T _C = 100 °C	-59	А
IDM	Pulsed Drain Current note1	-400	А
EAS	Single Pulsed Avalanche Energy note2	210	mJ
PD	Power Dissipation $T_C = 25^{\circ}C$	109	W
TJ, TSTG	Operating and Storage Temperature Range	-55 to +175	$^{\circ}$ C

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	Reuc	3.0	°C/W
Thermal Resistance, Junction-to-Ambient	Rеја	50	°C/W



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Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID= -250μA	-30	-	-	V
IDSS	Zero Gate Voltage Drain Current	VDS= -30V, VGS=0V,	-	-	-1	μΑ
IGSS	Gate to Body Leakage Current	VDS=0V, VGS= ±20V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID= -250μA	-1.0	-1.5	-2.5	V
	Static Drain-Source on-Resistance	VGS= -10V, ID= -30A	-	5.0	6.0	_
RDS(on)		VGS= -4.5V, ID= -20A	-	7.0	9.0	mΩ
Ciss	Input Capacitance	VDS= -15V, VGS=0V,	-	6560	-	pF
Coss	Output Capacitance	f=1.0MHz	-	742	-	pF
Crss	Reverse Transfer Capacitance		-	700	•	pF
Qg	Total Gate Charge	VDS= -15V, ID= -30A,	-	30	-	nC
Qgs	Gate-Source Charge	VGS= -10V	-	6	-	nC
Qgd	Gate-Drain("Miller") Charge		-	8	-	nC
td(on)	Turn-on Delay Time		-	11	-	ns
tr	Turn-on Rise Time	VDD= -15V, ID= -30A,	-	13	-	ns
td(off)	Turn-off Delay Time	VGS= -10V, RGEN=2.5Ω	-	52	-	ns
tf	Turn-off Fall Time		-	21	-	ns
IS	Maximum Continuous Drain to Source DiodeForward Current			ı	-100	А
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-400	Α
VSD	Drain to Source Diode Forward Voltage	VGS=0V, IS= -30 A		-0.8	-1.2	V

Notes:

- 1、Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- $2_{\rm N}$ E AS condition: T J =25 °C, V DD = -15V, V G = -10V, R G =25 Ω , L=0.5mH, I AS = -29A
- 3、Pulse Test: Pulse Width≤300µs, Duty Cycle≤2%

Typical Characteristics

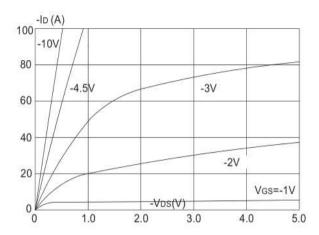


Figure1: Output Characteristics

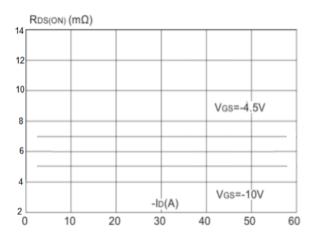


Figure 3:On-resistance vs. Drain Current

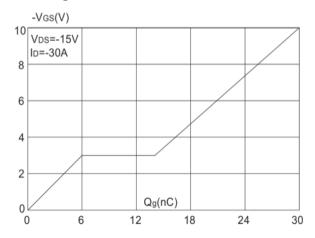


Figure 5: Gate Charge Characteristics

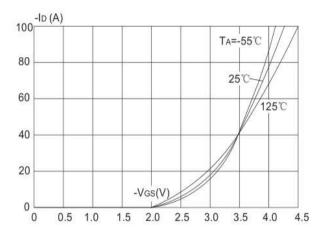


Figure 2: Typical Transfer Characteristics

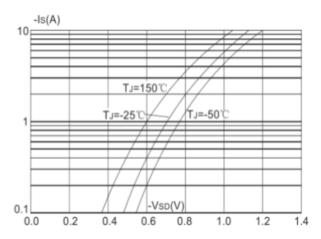


Figure 4: Body Diode Characteristics

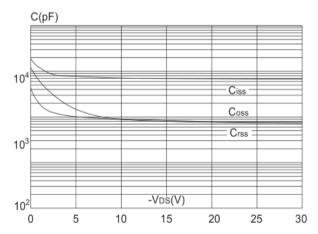


Figure 6: Capacitance Characteristics



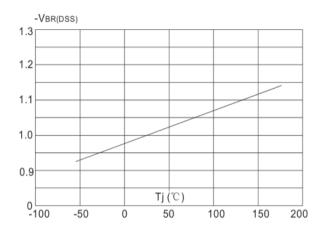


Figure 7: Normalized Breakdown Voltage vs.

Junction Temperature

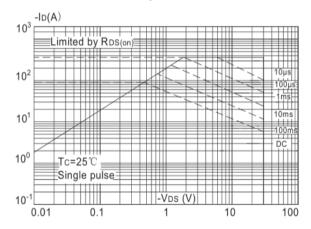


Figure 9: Maximum Safe Operating Area

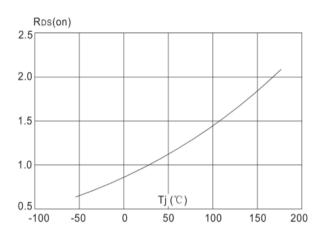


Figure 8: Normalized on Resistance vs.

Junction Temperature

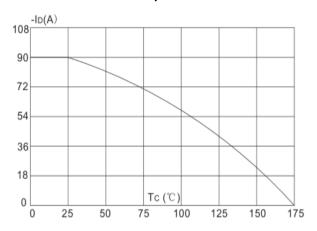


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

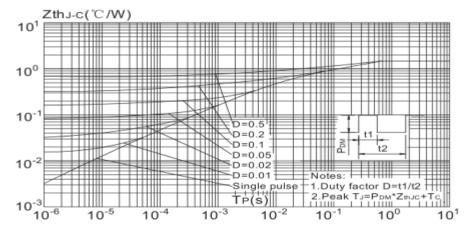


Figure.11: Maximum Effective

Transient Thermal Impedance, Junction-to-Case



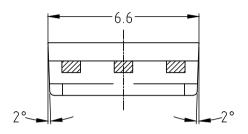
Ordering and Marking Information

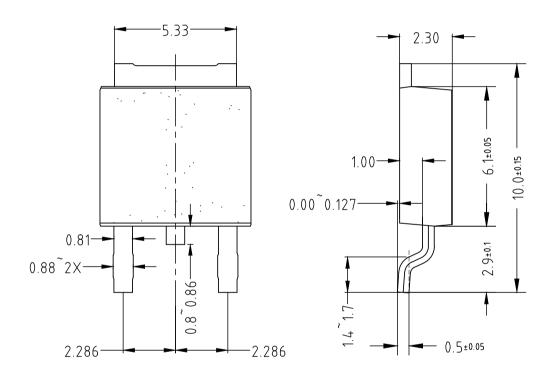
Ordering Device No.	Marking	Package	Packing	Quantity
ASDM30P100KQ-R	30P100	TO-252	Tape&Reel	2500/Reel

PACKAGE	MARKING
TO-252	30P100 Date Code

-30V P-Channel MOSFET

TO-252







ASDM30P100KQ

-30V P-Channel MOSFET

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